

P-Channel Enhancement Mode Power MOSFET

Description

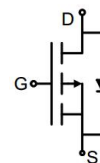
The G2K8P15S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

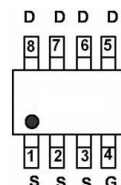
- V_{DS} -150V
- I_D (at $V_{GS} = -10V$) -2.2A
- $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 310m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



pin assignment



SOP-8

Ordering Information

Device	Package	Marking	Packaging
G2K8P15S	SOP-8	G2K8P15	4000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-150	V
Continuous Drain Current	I_D	-2.2	A
Pulsed Drain Current (note1)	I_{DM}	-8.8	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	2.5	W
Single pulse avalanche energy (note2)	E_{AS}	25	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$

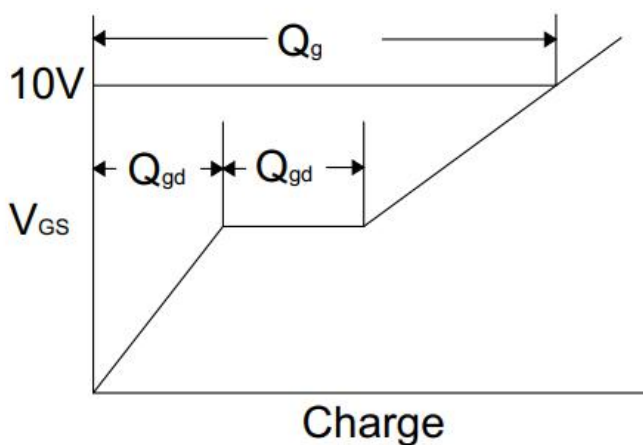
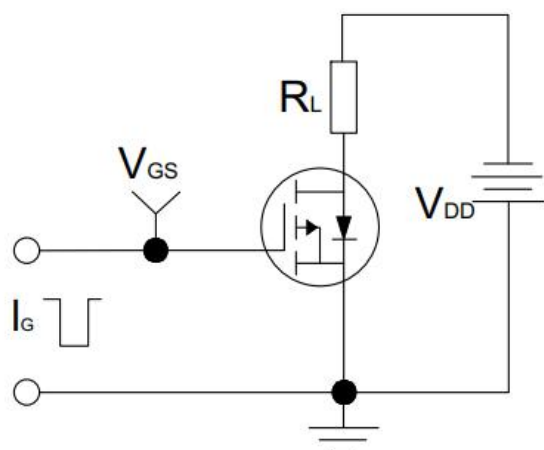
Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-150	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -150V, V_{GS} = 0V$	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-2.2	-3.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -1A$	--	277	310	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -15V, I_D = -1A$	--	7	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = -75V,$ $f = 1.0MHz$	--	966	--	pF
Output Capacitance	C_{oss}		--	39	--	
Reverse Transfer Capacitance	C_{rss}		--	24	--	
Total Gate Charge	Q_g	$V_{DD} = -75V,$ $I_D = -1A,$ $V_{GS} = -10V$	--	11	--	nC
Gate-Source Charge	Q_{gs}		--	3.2	--	
Gate-Drain Charge	Q_{gd}		--	1.9	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -75V,$ $I_D = -1A,$ $R_G = 6\Omega$	--	9.7	--	ns
Turn-on Rise Time	t_r		--	2.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	17	--	
Turn-off Fall Time	t_f		--	5.7	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ C$	--	--	-2.2	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ C, I_{SD} = -1A, V_{GS} = 0V$	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	$I_F = -1A, V_{GS} = 0V$ $di/dt = -100A/us$	--	157	--	nC
Reverse Recovery Time	T_{rr}		--	65	--	ns

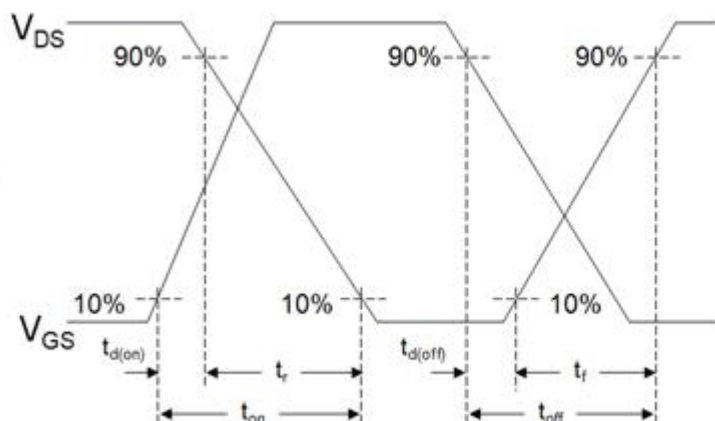
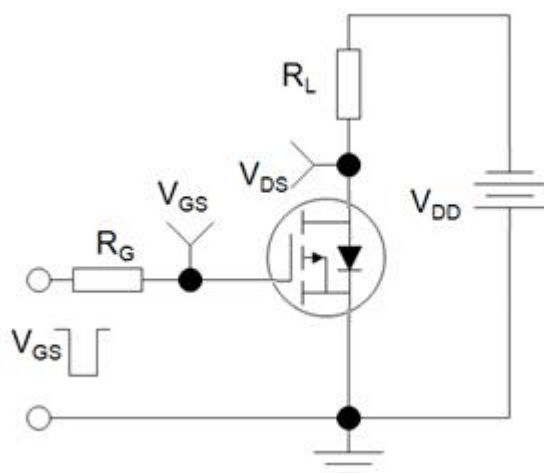
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : $T_J = 25^\circ\text{C}$, $V_{DD} = -50V$, $V_{GS} = -10V$, $L = 0.5mH$, $R_G = 25\Omega$
3. Identical low side and high side switch with identical R_G

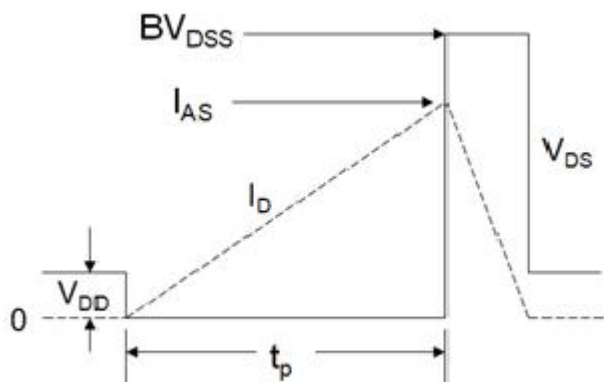
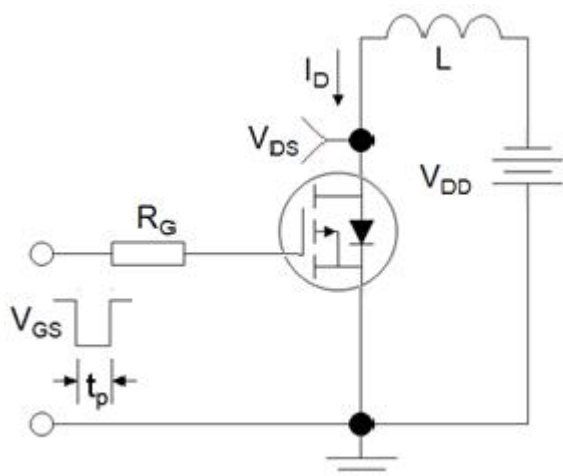
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

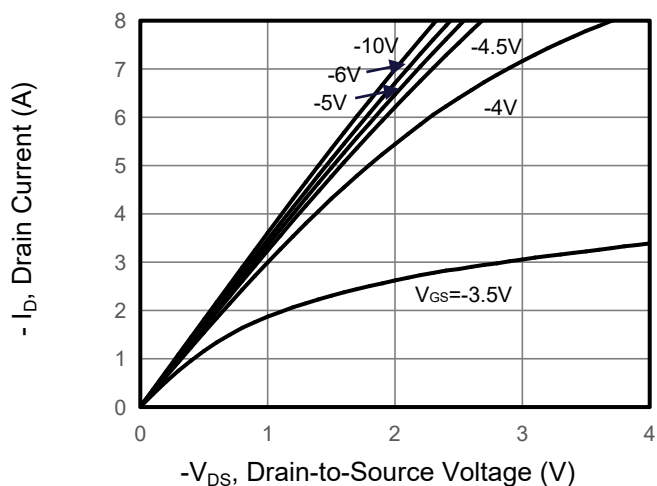


Figure 2. Transfer Characteristics

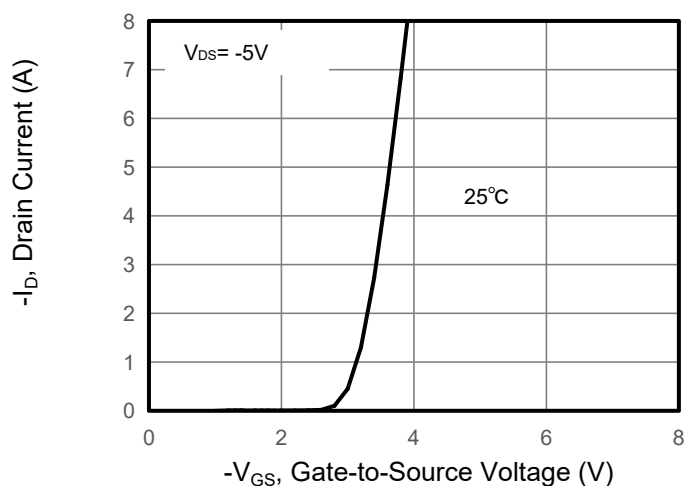


Figure 3. Drain Source On Resistance

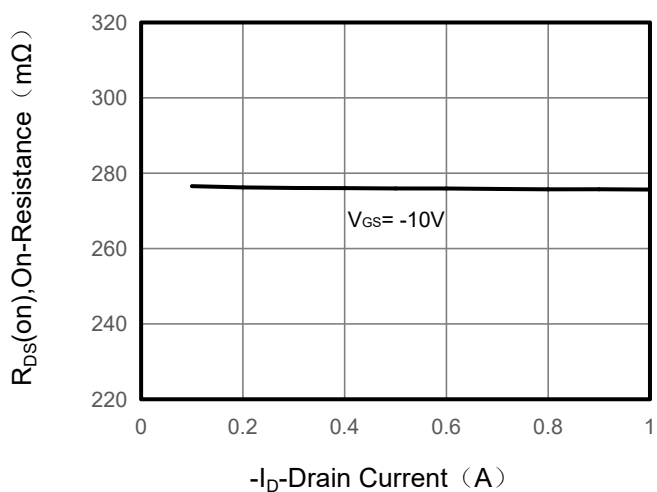


Figure 4. Gate Charge

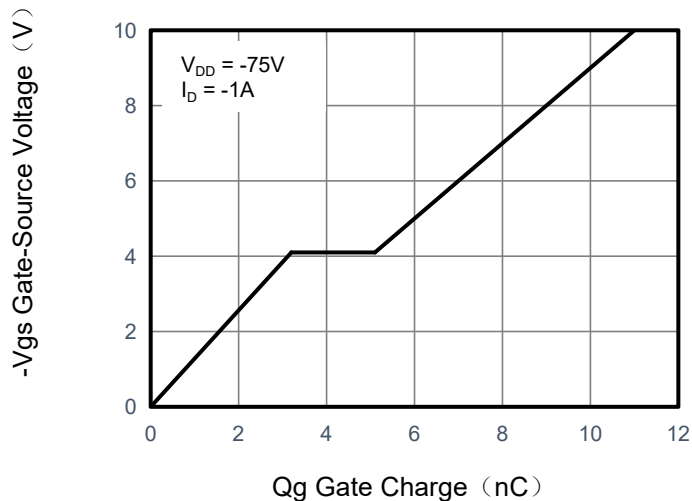


Figure 5. Capacitance

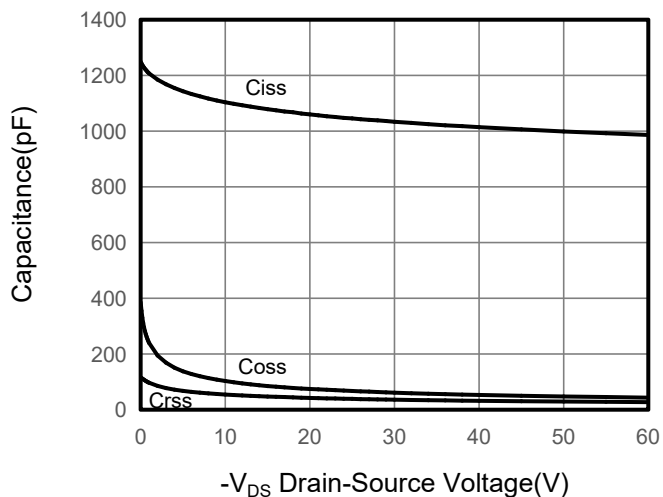
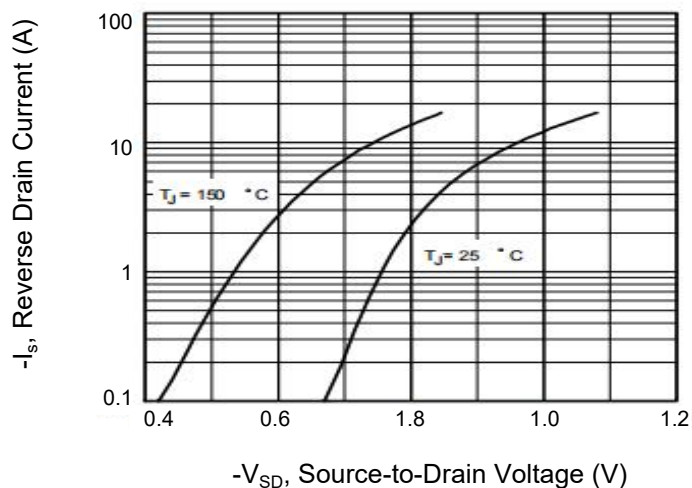


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

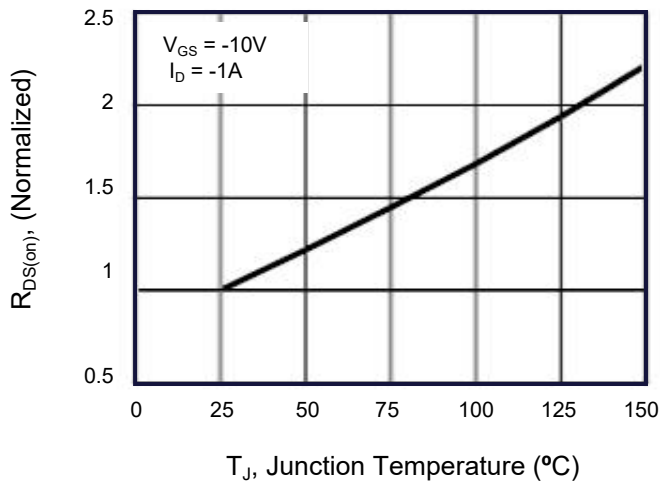


Figure 8. Safe Operation Area

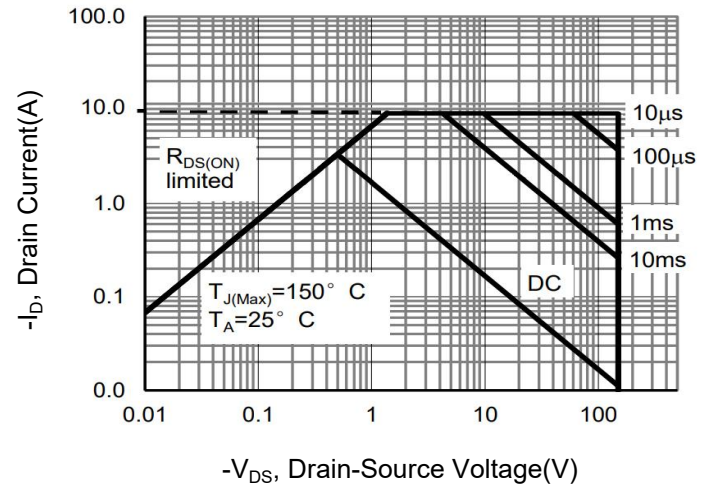
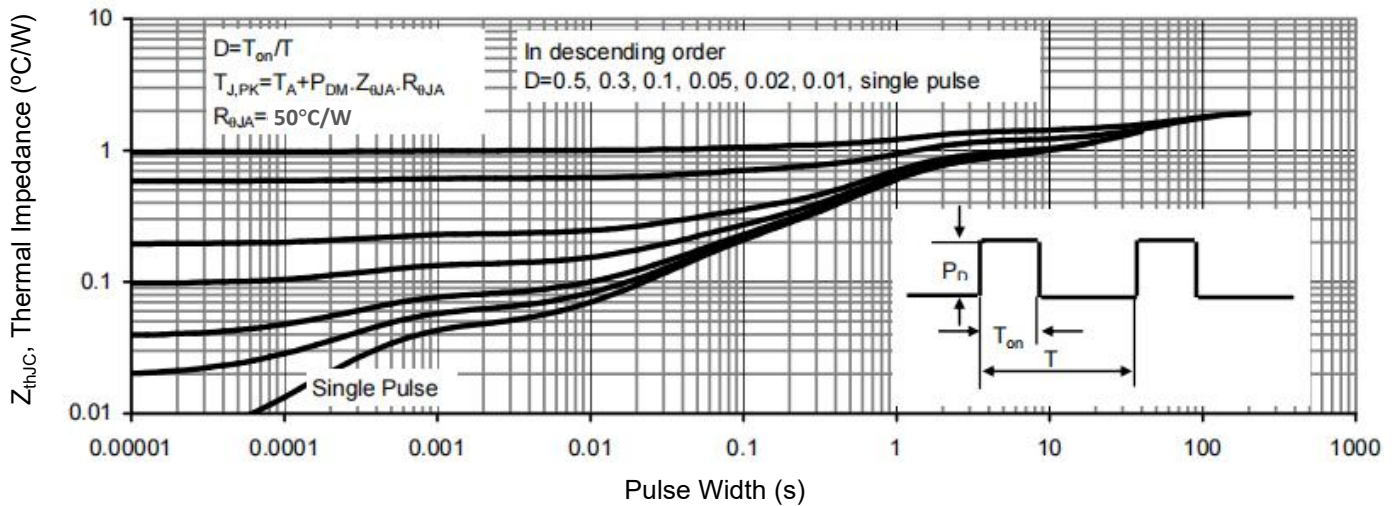
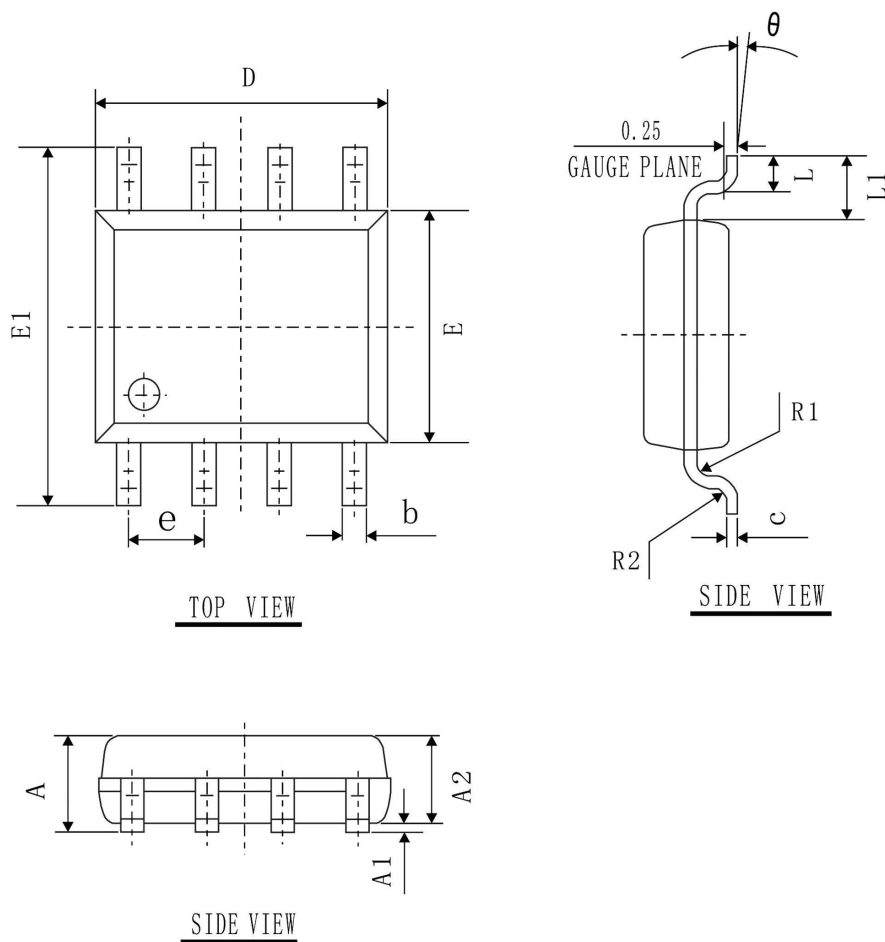


Figure 9. Normalized Maximum Transient Thermal Impedance



SOP-8 Package information



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L 1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		